

**IN THE CLAIMS**

Please cancel claims 30 and 31, without prejudice or disclaimer.

Please amend claims 29 and 32 as follows:

29. (Twice Amended) A method of co-planarizing copper or copper-based metallurgy and a refractory metal-based barrier layer or liner in an interlevel dielectric layer of a semiconductor device comprising the steps of:

planarizing said copper or copper-based metallurgy using a first slurry comprising an oxidizing agent comprising ferric nitrate, an oxidation inhibitor, a surfactant comprising sodium octyl sulfate and an abrasive comprising alumina in water; said first slurry having a pH of between 1.2 and 2.5 and said first slurry for removing copper selectively with respect to said barrier layer or liner; and

co-planarizing said barrier layer or liner and said interlevel dielectric layer using a second slurry comprising a peroxide agent, an oxidation inhibitor, a surfactant comprising sodium octyl sulfate, and an abrasive comprising silica in water; said second slurry having a pH of between 3.0 and 7.5 and said second slurry for removing said barrier layer or liner.

32. (Once Amended) The method of claim 33, wherein the first removal rate is about eight times greater than the second removal rate.

Please add the following new claim:

33. The method of claim 29, wherein said second slurry removes said barrier layer or liner at a first removal rate and copper at a second removal rate, the first removal rate greater than the second removal rate.